Vishay Siliconix

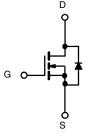
Automotive N-Channel 40 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | |
|--|--------|--|--|--|
| V _{DS} (V) | 40 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$ | 0.0017 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$ | 0.0020 | | | |
| I _D (A) | 200 | | | |
| Configuration | Single | | | |

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Thin 1.9 mm height
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





N-Channel MOSFET

| ORDERING INFORMATION | |
|---------------------------------|-----------------|
| Package | PowerPAK 8x8L |
| Lead (Pb)-free and Halogen-free | SQJQ402E-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS | $T_C = 25 ^{\circ}C$, unles | ss otherwise noted |) | |
|--|---|-----------------------------------|-------------|----|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V _{DS} | 40 | V |
| Gate-Source Voltage | | V_{GS} | ± 20 | V |
| Continuous Drain Current | T _C = 25 °C a | 1 | 200 | |
| Continuous Drain Current | T _C = 125 °C | l _D | 127 | |
| Continuous Source Current (Diode Conduction | I _S | 200 | Α | |
| Pulsed Drain Current ^b | | I _{DM} | 300 | |
| Single Pulse Avalanche Current L = 0.1 mH | | I _{AS} | 85 | |
| Single Pulse Avalanche Energy | | E _{AS} | 361 | mJ |
| Maximum Dower Dissipation | T _C = 25 °C | В | 150 | W |
| Maximum Power Dissipation | T _C = 125 °C | P _D | 50 | VV |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C |
| Soldering Recommendations (Peak Temperate | Soldering Recommendations (Peak Temperature) d, e | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------|-------------|------------|-------|------|
| PARAMETER | | SYMBOL | LIMIT | UNIT |
| Junction-to-Ambient | PCB Mount c | R_{thJA} | 50 | °C/W |
| Junction-to-Case (Drain) | | R_{thJC} | 1 | C/VV |

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300 \,\mu\text{s}$, duty cycle $\leq 2 \,\%$.
- c. When mounted on 1" square Pcb (Fr4 material).
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK 8x8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT | |
|-------------------------------------|---------------------------|---|---|------|--------|--------|---|--|
| Static | | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | V _{GS} | = 0, I _D = 250 μA | 40 | - | - | ., | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | = V _{GS} , I _D = 250 μA | 1.5 | 2 | 2.5 | V | |
| Gate-Source Leakage | I _{GSS} | V _{DS} = | 0 V, V _{GS} = ± 20 V | - | - | ± 100 | nA | |
| | | $V_{GS} = 0 V$ | V _{DS} = 40 V | - | - | 1 | | |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 125 °C | - | - | 50 | μΑ | |
| | | V _{GS} = 0 V | V _{DS} = 40 V, T _J = 175 °C | - | - | 150 | V 5 V 000 nA 0 μA 0 μA 0 A 017 020 026 031 S 000 pF 0 nC 5 Ω 0 ns | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | V _{DS} ≥ 5 V | 100 | - | - | Α | |
| | | V _{GS} = 10 V | I _D = 20 A | - | 0.0013 | 0.0017 | 0.0020 0.0026 0.0031 - S | |
| Dunin Course On Chata Basistana 8 | Б | V _{GS} = 4.5 V | I _D = 10 A | - | 0.0015 | 0.0020 | | |
| Drain-Source On-State Resistance a | R _{DS(on)} | V _{GS} = 10 V | I _D = 20 A, T _J = 125 °C | - | - | 0.0026 | | |
| | | V _{GS} = 10 V | I _D = 20 A, T _J = 175 °C | - | - | 0.0031 | | |
| Forward Transconductance b | 9 _{fs} | V _{DS} = 15 V, I _D = 20 A | | - | 140 | - | S | |
| Dynamic ^b | | | | | | | | |
| Input Capacitance | C _{iss} | | | - | 10 760 | 13 500 | | |
| Output Capacitance | C _{oss} | $V_{GS} = 0 V$ | $V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$ | = | 1370 | 1800 | pF | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 650 | 850 | | |
| Total Gate Charge ^c | Q_g | | | =. | 169 | 260 | | |
| Gate-Source Charge c | Q _{gs} | $V_{GS} = 10 \text{ V}$ | $V_{DS} = 20 \text{ V}, I_{D} = 40 \text{ A}$ | = | 32 | - | nC | |
| Gate-Drain Charge c | Q_{gd} | | | = | 29 | - | | |
| Gate Resistance | R_g | | f = 1 MHz | 0.6 | 1.3 | 2.5 | Ω | |
| Turn-On Delay Time ^c | t _{d(on)} | | | - | 19 | 30 | | |
| Rise Time ^c | t _r | V _{DD} = | $V_{DD} = 20 \text{ V}, R_1 = 0.5 \Omega$ | | 15 | 25 |] " | |
| Turn-Off Delay Time ^c | t _{d(off)} | $I_D \cong 40 \text{ A},$ | $V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | - | 69 | 110 | IIS | |
| Fall Time ^c | t _f | | | - | 11 | 20 | | |
| Source-Drain Diode Ratings and Cha | racteristics ^b | | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 300 | Α | |
| Forward Voltage | V_{SD} | 1 | = 50 A, V _{GS} = 0 | | 0.82 | 1.2 | V | |

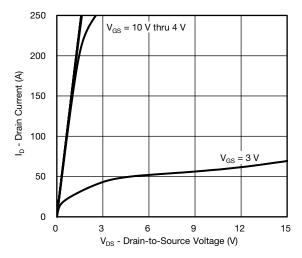
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

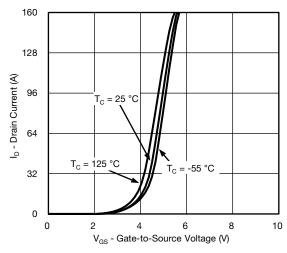
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



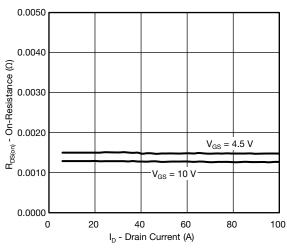
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



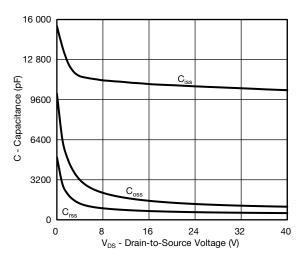
Output Characteristics



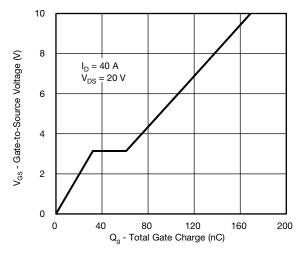
Transfer Characteristics



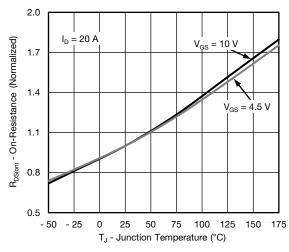
On-Resistance vs. Drain Current



Capacitance



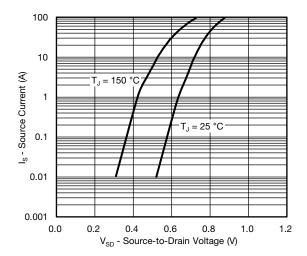
Gate Charge



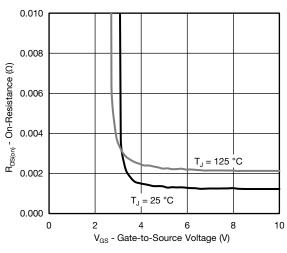
On-Resistance vs. Junction Temperature



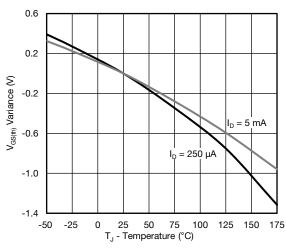
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



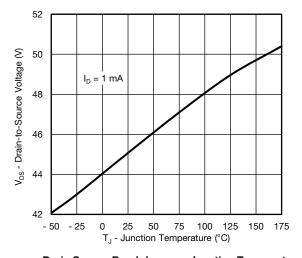
Source Drain Diode Forward Voltage



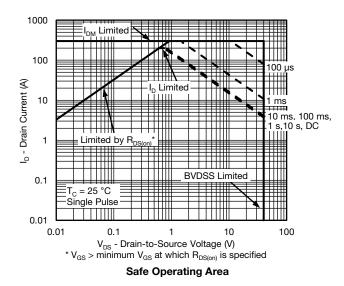
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

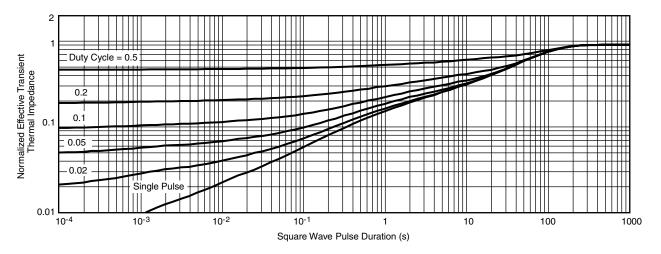


Drain Source Breakdown vs. Junction Temperature

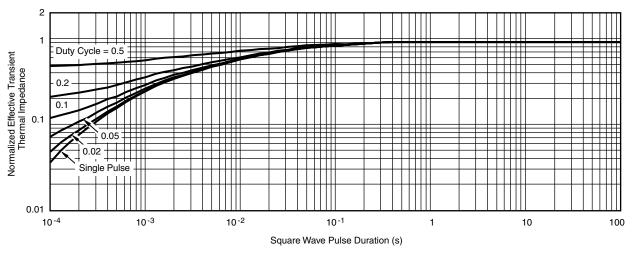




THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

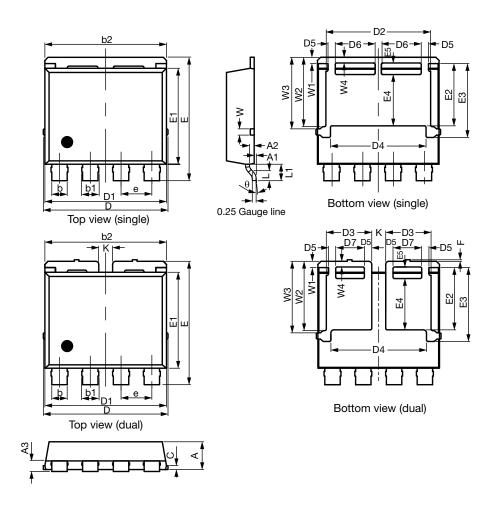


Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62748.



PowerPAK® 8 x 8L Case Outline



| DIM | | MILLIMETERS | | INCHES | | | |
|------|------|-------------|------|--------|-----------|-------|--|
| DIM. | MIN. | NOM. | MAX. | MIN. | MIN. NOM. | | |
| Α | 1.70 | 1.80 | 1.90 | 0.067 | 0.071 | 0.075 | |
| A1 | 0.00 | 0.08 | 0.13 | 0.000 | 0.003 | 0.005 | |
| A2 | 0.25 | 0.30 | 0.35 | 0.010 | 0.012 | 0.014 | |
| A3 | 0.55 | 0.62 | 0.70 | 0.022 | 0.024 | 0.028 | |
| b | 0.92 | 1.00 | 1.08 | 0.036 | 0.039 | 0.043 | |
| b1 | 1.02 | 1.10 | 1.18 | 0.040 | 0.043 | 0.046 | |
| b2 | 7.80 | 7.90 | 8.00 | 0.307 | 0.311 | 0.315 | |
| С | 0.20 | 0.25 | 0.30 | 0.008 | 0.010 | 0.012 | |
| D | 8.00 | 8.10 | 8.25 | 0.315 | 0.319 | 0.325 | |
| D1 | 7.80 | 7.90 | 8.00 | 0.307 | 0.311 | 0.315 | |
| D2 | 6.70 | 6.80 | 6.90 | 0.264 | 0.268 | 0.272 | |
| D3 | 2.85 | 2.95 | 3.05 | 0.112 | 0.116 | 0.120 | |
| D4 | 6.11 | 6.21 | 6.31 | 0.241 | 0.244 | 0.248 | |
| D5 | 0.37 | 0.47 | 0.57 | 0.015 | 0.019 | 0.022 | |
| D6 | 2.49 | 2.59 | 2.69 | 0.098 | 0.102 | 0.106 | |
| D7 | 1.76 | 1.86 | 1.96 | 0.069 | 0.073 | 0.077 | |

Revision: 16-Oct-17 1 Document Number: 67734





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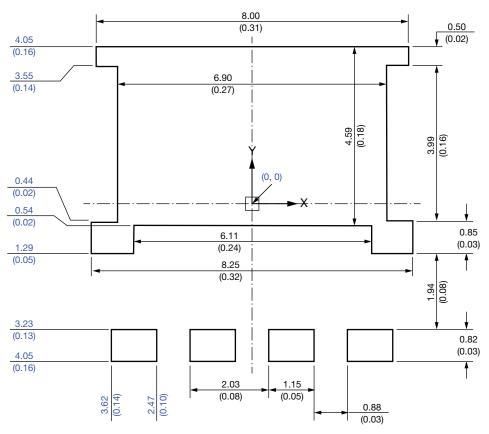
| D114 | | MILLIMETERS | | INCHES | | | |
|------|------|-------------|------|--------|-------|-------|--|
| DIM. | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. | |
| е | 1.95 | 2.00 | 2.05 | 0.077 | 0.079 | 0.081 | |
| E | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 | |
| E1 | 6.12 | 6.22 | 6.32 | 0.241 | 0.245 | 0.249 | |
| E2 | 3.94 | 4.04 | 4.14 | 0.140 | 0.159 | 0.163 | |
| E3 | 4.69 | 4.79 | 4.89 | 0.185 | 0.189 | 0.193 | |
| E4 | 3.23 | 3.33 | 3.43 | 0.127 | 0.131 | 0.135 | |
| E5 | 0.65 | 0.75 | 0.85 | 0.026 | 0.030 | 0.033 | |
| F | 0.00 | 0.10 | 0.15 | 0.000 | 0.004 | 0.006 | |
| L | 0.62 | 0.72 | 0.82 | 0.024 | 0.028 | 0.032 | |
| L1 | 0.92 | 1.07 | 1.22 | 0.036 | 0.042 | 0.048 | |
| K | 0.80 | 0.90 | 1.00 | 0.031 | 0.035 | 0.039 | |
| W | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| W1 | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.020 | |
| W2 | 4.39 | 4.49 | 4.59 | 0.173 | 0.177 | 0.181 | |
| W3 | 4.54 | 4.64 | 4.74 | 0.179 | 0.183 | 0.187 | |
| W4 | 0.32 | 0.37 | 0.42 | 0.013 | 0.015 | 0.017 | |
| θ | 6° | 10° | 14° | 6° | 10° | 14° | |

C17-1388-Rev. B, 16-Oct-17

DWG: 6026



Recommended Minimum PADs for PowerPAK® 8 x 8L Single



Dimensions in millimeters (inches)

Note

• Linear dimensions are in black, the same information is provided in ordinate dimensions which are in blue.



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